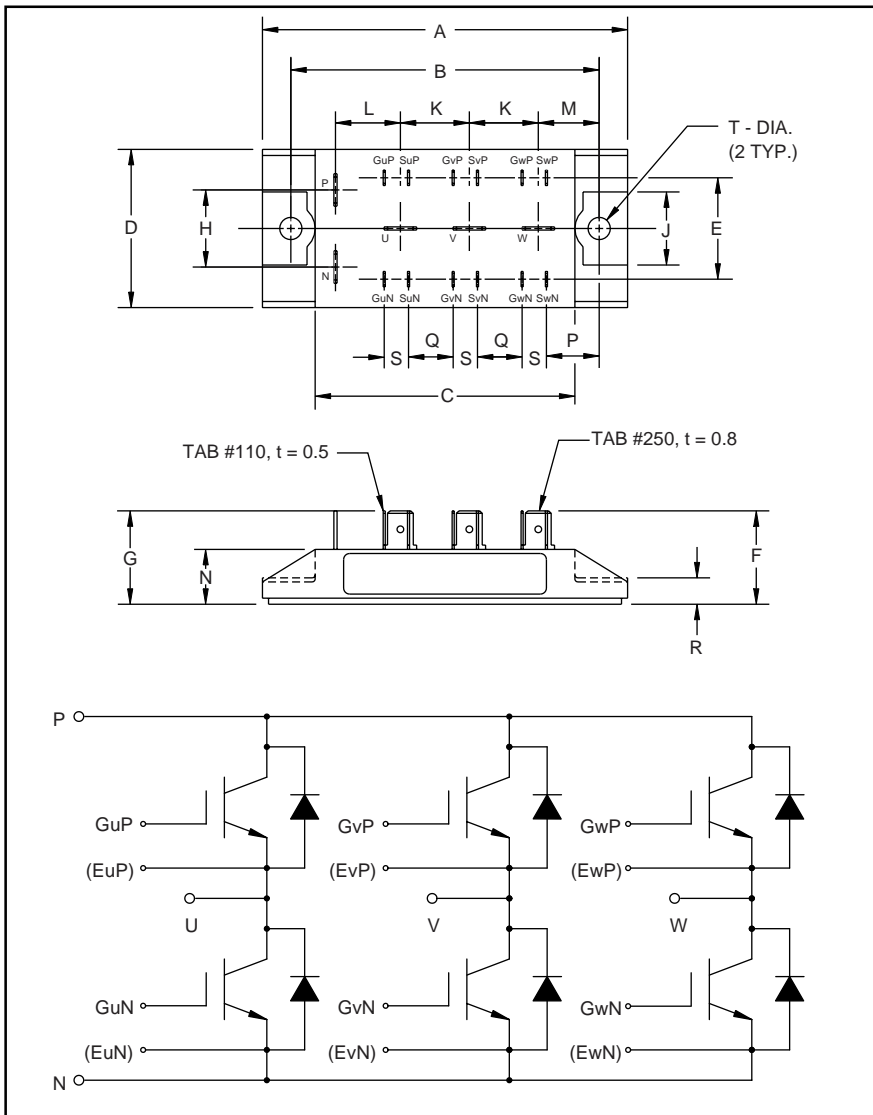


MITSUBISHI IGBT MODULES

CM15TF-12H

MEDIUM POWER SWITCHING USE
INSULATED TYPE



Outline Drawing and Circuit Diagram

| Dimensions | Inches | Millimeters |
|------------|-----------|-------------|
| A | 3.54 | 90.0 |
| B | 2.99±0.01 | 76.0±0.2 |
| C | 2.52 | 64.0 |
| D | 1.54 | 39.0 |
| E | 0.98 | 25.0 |
| F | 0.90 | 23.0 |
| G | 0.87 | 22.0 |
| H | 0.75 | 19.0 |
| J | 0.71 | 18.0 |

| Dimensions | Inches | Millimeters |
|------------|-----------|-------------|
| K | 0.67 | 17.0 |
| L | 0.63 | 16.0 |
| M | 0.59 | 15.0 |
| N | 0.56 | 14.1 |
| P | 0.51 | 13.0 |
| Q | 0.43 | 11.0 |
| R | 0.26 | 6.5 |
| S | 0.24 | 6.0 |
| T | 0.22 Dia. | Dia. 5.5 |



Description:

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of six IGBTs in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- High Frequency Operation
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM15TF-12H is a 600V (V_{CES}), 15 Ampere Six-IGBT Module.

| Type | Current Rating Amperes | V_{CES} Volts (x 50) |
|------|---------------------------|---------------------------|
| CM | 15 | 12 |

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Absolute Maximum Ratings, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

| Ratings | Symbol | CM15TF-12H | Units |
|---|-----------|-------------|------------------|
| Junction Temperature | T_j | -40 to +150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -40 to +125 | $^\circ\text{C}$ |
| Collector-Emitter Voltage (G-E SHORT) | V_{CES} | 600 | Volts |
| Gate-Emitter Voltage (C-E SHORT) | V_{GES} | ± 20 | Volts |
| Collector Current ($T_C = 25\text{ }^\circ\text{C}$) | I_C | 15 | Amperes |
| Peak Collector Current | I_{CM} | 30* | Amperes |
| Emitter Current** ($T_C = 25\text{ }^\circ\text{C}$) | I_E | 15 | Amperes |
| Peak Emitter Current** | I_{EM} | 30* | Amperes |
| Maximum Collector Dissipation ($T_C = 25\text{ }^\circ\text{C}$, $T_j \leq 150\text{ }^\circ\text{C}$) | P_c | 100 | Watts |
| Mounting Torque, M5 Mounting | - | 1.47 ~ 1.96 | N · m |
| Weight | - | 150 | Grams |
| Isolation Voltage (Main Terminal to Baseplate, AC 1 min.) | V_{iso} | 2500 | Vrms |

*Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|--------------------------------------|---------------|--|------|------|-------|---------------|
| Collector-Cutoff Current | I_{CES} | $V_{CE} = V_{CES}$, $V_{GE} = 0V$ | - | - | 1.0 | mA |
| Gate Leakage Current | I_{GES} | $V_{GE} = V_{GES}$, $V_{CE} = 0V$ | - | - | 0.5 | μA |
| Gate-Emitter Threshold Voltage | $V_{GE(th)}$ | $I_C = 1.5\text{mA}$, $V_{CE} = 10V$ | 4.5 | 6.0 | 7.5 | Volts |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = 15A$, $V_{GE} = 15V$ | - | 2.1 | 2.8** | Volts |
| | | $I_C = 15A$, $V_{GE} = 15V$, $T_j = 150\text{ }^\circ\text{C}$ | - | 2.15 | - | Volts |
| Total Gate Charge | Q_G | $V_{CC} = 300V$, $I_C = 15A$, $V_{GE} = 15V$ | - | 45 | - | nC |
| Emitter-Collector Voltage | V_{EC} | $I_E = 15A$, $V_{GE} = 0V$ | - | - | 2.8 | Volts |

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

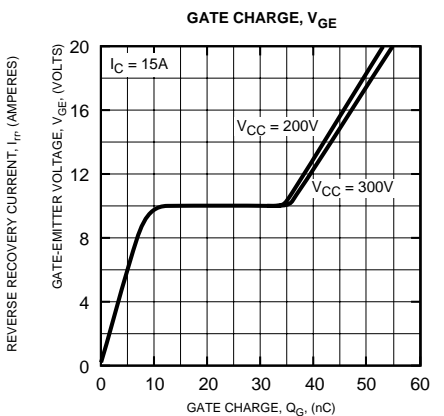
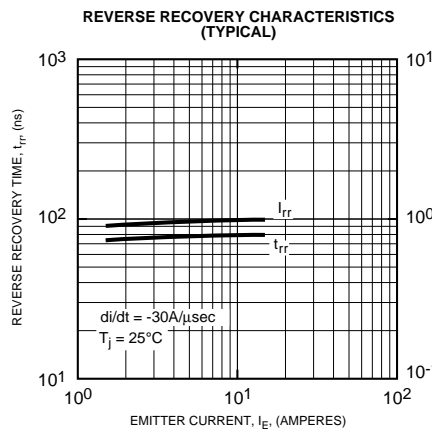
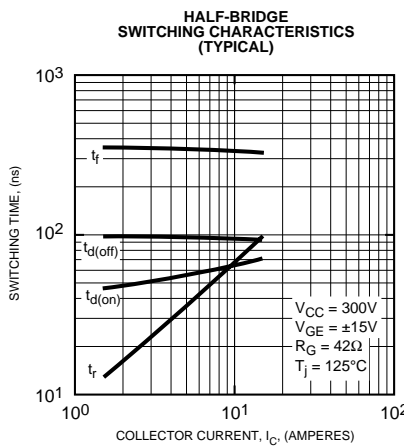
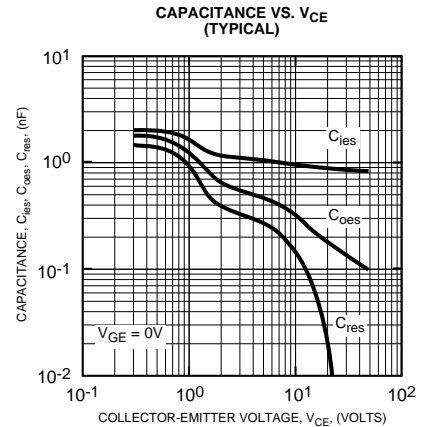
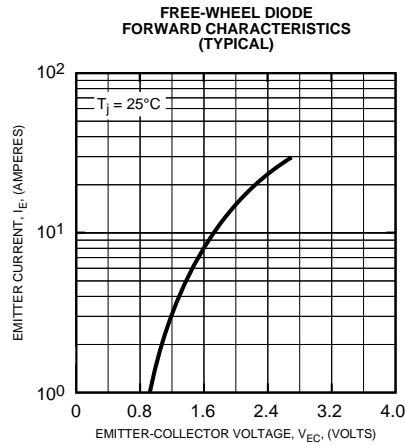
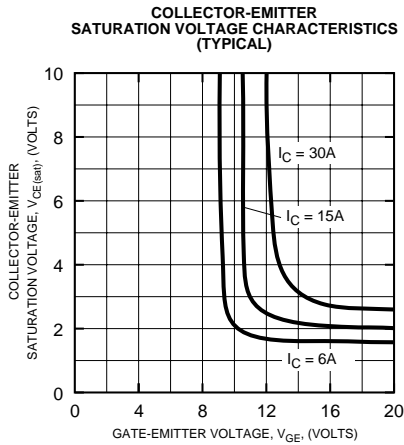
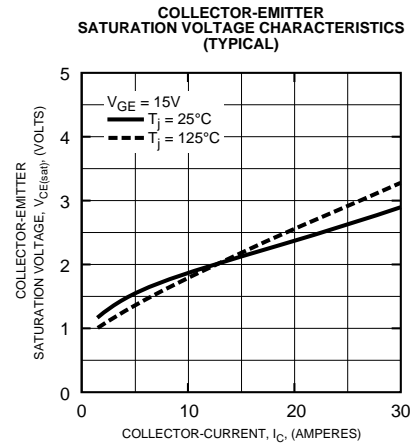
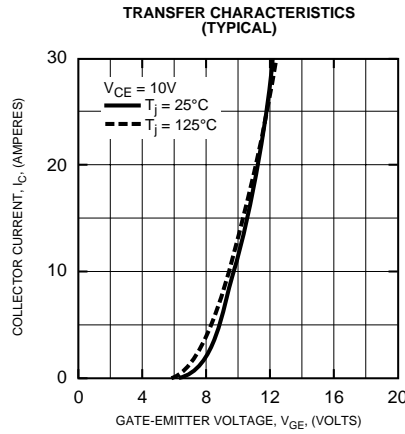
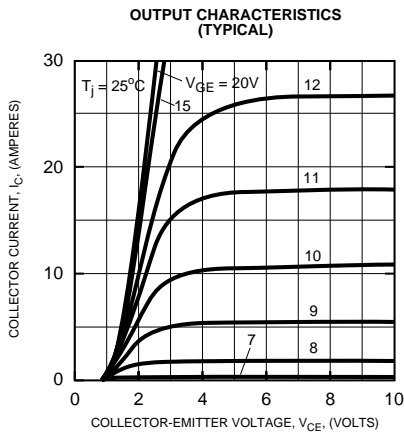
| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|-------------------------------|---------------------|--|------|------|------|---------------|
| Input Capacitance | C_{ies} | | - | - | 1.5 | nF |
| Output Capacitance | C_{oes} | $V_{GE} = 0V$, $V_{CE} = 10V$ | - | - | 0.5 | nF |
| Reverse Transfer Capacitance | C_{res} | | - | - | 0.3 | nF |
| Resistive | Turn-on Delay Time | $V_{CC} = 300V$, $I_C = 15A$, | - | - | 120 | ns |
| | Rise Time | | | | | |
| Load | Turn-off Delay Time | $V_{GE1} = V_{GE2} = 15V$, $R_G = 42\Omega$ | - | - | 300 | ns |
| | Fall Time | | | | | |
| Switching | | | - | - | 200 | ns |
| Diode Reverse Recovery Time | t_{rr} | $I_E = 15A$, $di_E/dt = -30A/\mu\text{s}$ | - | - | 110 | ns |
| Diode Reverse Recovery Charge | Q_{rr} | $I_E = 15A$, $di_E/dt = -30A/\mu\text{s}$ | - | 0.04 | - | μC |

Thermal and Mechanical Characteristics, $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|--------------------------------------|---------------|------------------------------------|------|------|-------|--------------------|
| Thermal Resistance, Junction to Case | $R_{th(j-c)}$ | Per IGBT | - | - | 1.30 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Case | $R_{th(j-c)}$ | Per FWDi | - | - | 3.50 | $^\circ\text{C/W}$ |
| Contact Thermal Resistance | $R_{th(c-f)}$ | Per Module, Thermal Grease Applied | - | - | 0.092 | $^\circ\text{C/W}$ |

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